



Wireless Components

3-Band Digital TV / Set-Top-Box Tuner IC TUA6034, TUA6036 'TAIFUN' Version 2.4

Specification March 2003

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div.	div.	in extended mode reference division ratio of 80 replaced by 32	
5-2	5-2	new definition of thermal properties	

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div.	div.	status: preliminary	
div.	div.	bug fixes: TSSOP and VQFN pinning. Changes: application focus to digital applications, tbd's replaced by values	
5-10, 5-11	5-10, 5-11	phase noise values added	
5-21	5-21	diagrams added	

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div.	div	Stand-by mode added
5-5	5-5	Crystal Oscillator: Input impedances added
5-7	5-7	Output leakage current replaced by port output voltage Symbol for port output saturation voltages changed
5-12	5-12	AGC source current 2 and AGC output voltage changed
5-15	5-15	Definition for MA1= 0 and MA0 = 1 changed

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5-5	5-5	MID band: I _{VCC} corrected	
5-10, 5-11	5-10, 5-11	Phase Noise: new values	
5-12	5-12	AGC output voltage changed	

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5-6	5-6	Bus output SDA, Low-level output voltage, I _{OL} = 6 mA at 400 kHz deleted	

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5-6	5-6	Bus output SDA, Low-level output voltage, I _{OL} = 6 mA at 400 kHz deleted	
3-2 ff	3-2 ff	Pinning of TUA6034-V changed	

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all	all	Mirrored version TUA6036 added	
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Version)	Version)		
2-10, 4-29, 4-30	2-10, 4-29, 4-30	Frequencies corrected	
5-34	5-34	Ambient temperature extended	
5-38, 5-39, 5-40	5-38, 5-39, 5-40	Input IP2,Input IIP3, Output voltage causing 1 dB compression added, test frequencies changed	

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Product Info

Product Info

General Description

The **TUA6034**, **TUA6036** '**TAIFUN**' device combines a mixer-oscillator block with a digitally programmable phase locked loop (PLL) for use in TV and VCR tuners and in set-top-box applications.

Features

General

- Suitable for PAL, NTSC, DVB and ATSC
- Wideband AGC detector for internal tuner AGC
 - 5 programmable take-over points
 - 2 programmable time constants
- Low phase noise
- Full ESD protection

Mixer/Oscillator

- High impedance mixer input (common emitter) for LOW band
- Low impedance mixer input (common base) for MID band
- Low impedance mixer input (common base) for HIGH band
- 2 pin oscillator for LOW band
- 2 pin oscillator for MID band
- 4 pin oscillator for HIGH band

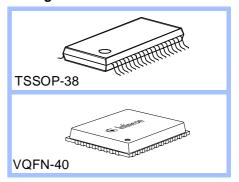
IF-Amplifier

 Symmetrical IF preamplifier with low output impedance able to drive a compensated SAW filter (500 Ω// 40 pF)

Application

 The IC is suitable for PAL, NTSC, DVB-C, DVB-T and ATSC tuners.
 The focus is on digital terrestrial.

Package



PLL

- 4 independent I²C addresses
- I²C bus protocol compatible with 3.3 V and 5V micro-controllers up to 400 kHz
- High voltage VCO tuning output
- 4 PNP ports
- 1 NPN port/ADC input
- Internal LOW/MID/HIGH band switch
- Stand-by mode
- Lock-in flag
- 6 programmable reference divider ratios (24, 28, 32, 64, 80, 128)
- 4 programmable charge pump currents

The AGC stage makes the tuner AGC independent of the Video-IF AGC.

Ordering Information

Туре	Ordering Code	Package
TUA6034-T	Q67034-H0009	P-TSSOP-38
TUA6036-T	Q67037-A0012	P-TSSOP-38
TUA6034-V	Q67034-H0008	P-VQFN-40 (on request)

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Product Description

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Product Description

2.1 Overview

The **TUA6034**, **TUA6036** '**TAIFUN**' device combines a mixer-oscillator block with a digitally programmable phase locked loop (PLL) for use in TV and VCR tuners and in set-top-box applications.

The mixer-oscillator block includes three balanced mixers (one mixer with an unbalanced high-impedance input and two mixers with a balanced low-impedance input), two 2-pin asymmetrical oscillators for the LOW and the MID band, one 4-pin symmetrical oscillator for the HIGH band, an IF amplifier, a reference voltage, and a band switch.

The PLL block with four independently selectable chip addresses forms a digitally programmable phase locked loop. With a 4 MHz quartz crystal, the PLL permits precise setting of the frequency of the tuner oscillator up to 1024 MHz in increments of 31.25, 50, 62.5, 125, 142.86 or 166.7 kHz. The tuning process is controlled by a microprocessor via an I²C bus. The device has 5 output ports, one of them (P4) can also be used as ADC input port. A flag is set when the loop is locked. The lock flag can be read by the processor via the I²C bus.

2.2 Features

General

- Suitable for PAL, NTSC, DVB and ATSC
- Wideband AGC detector for internal tuner AGC
 - 5 programmable take-over points
 - 2 programmable time constants
- Low phase noise
- Full ESD protection

Mixer/Oscillator

- High impedance mixer input (common emitter) for LOW band
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- 2 pin oscillator for LOW band
- 2 pin oscillator for MID band
- 4 pin oscillator for HIGH band

IF-Amplifier

Symmetrical IF preamplifier with low output impedance able to drive a compensated SAW filter (500 Ω //40 pF)

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- 4 independent I²C addresses
- I²C bus protocol compatible with 3.3 V and 5V micro-controllers up to 400 kHz
- High voltage VCO tuning output
- 4 PNP ports
- 1 NPN port/ADC input
- Stand-by mode
- Internal LOW/MID/HIGH band switch
- Lock-in flag
- 6 programmable reference divider ratios (24, 28, 32, 64, 80, 128)
- 4 programmable charge pump currents

2.3 Application

- The IC is suitable for PAL, NTSC, DVB-C, DVB-T and ATSC tuners. The focus is on digital terrestrial.
- The AGC stage makes the tuner AGC independent of the Video-IF AGC.

Recommended band limits in MHz:

Table 2-1 ATSC tuners						
	RF input		Osci	llator		
Band	min	max	min	max		
LOW	55.25	157.25	101	203		
MID	163.25	451.25	201	479		
HIGH	457.25	861.25	503	907		

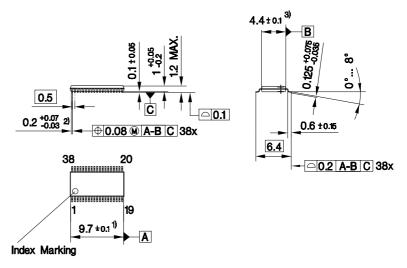
Table 2-2 DVB-T tuners						
	RF i	nput	Osci	llator		
Band	min	max	min	max		
LOW	48.25	154.25	87.15	193.15		
MID	161.25	439.25	200.15	478.15		
HIGH	447.25	863.25	486.15	902.15		

Note: Tuning margin of 3 MHz not included.



2.4 Package Outlines

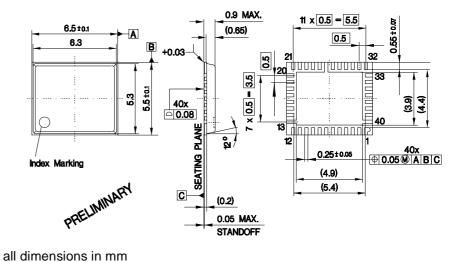
2.4.1 P-TSSOP-38



- 1) Does not include plastic or metal protrusion of 0.15 max. per side
- 2) Does not include dambar protrusion of 0.08 max. per side
- 3) Does not include plastic or metal protrusion of 0.25 max. per side

all dimensions in mm

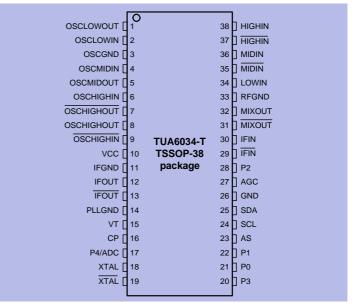
2.4.2 VQFN-40



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3.4.2	PLL block
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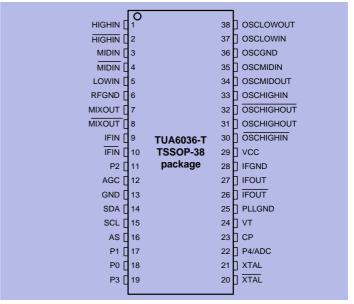


3.1 Pin Configuration



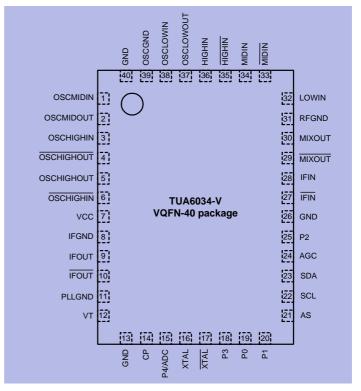
TUA6034 Pinconfig TSSOP

Figure 3-1 Pin Configuration TUA6034 in TSSOP-38 Package



TUA6036 Pinconfig TSSOP

Figure 3-2 Pin Configuration TUA6036 in TSSOP-38 Package



TUA6034 Pinconfig VQFN

Figure 3-3 Pin Configuration VQFN-40 Package

3.2 Pin Definition and Function

Table	Table 3-1 Pin Definition and Function						
Pin N	lo.	Symbol	Equivalent I/O-Schematic	Average DC voltage		oltage	
TS- SO P 38	VQ - FN 40		pin designation in parenthesis refer to VQFN40 package	LOW	MID	HIGH	
1/38	37	OSCLOW- OUT	2 (38)	2.1V			
2/ 37	38	OSCLOWIN		1.45 V			
3/ 36	39	OSCGND	oscillator ground	0.0 V	0.0 V	0.0 V	
4/ 35	1	OSCMIDIN	5 (2)		1.45V		
5/ 34	2	OSCMID- OUT	4 (1)		2.1 V		



Table 3-1 Pin Definition and Function (continued)						
Pin	Pin	Symbol	Equivalent I/O-Schematic	Avera	age DC vo	ltage
No.	No			LOW	MID	HIGH
6/ 33	3	OSCHIGHIN	ДД			1.5 V
7/ 32	4	OSCHIG- OUT	7 (4) 8 (5)			2.4 V
8/ 31	5	OSCHIG- OUT	9 (6)			2.4 V
9/ 30	6	OSCHIGHIN	<u> </u>			1.5 V
10/ 29	7	VCC	supply voltage	5.0 V	5.0 V	5.0 V
11/ 28	8	IFGND	IF ground	0.0 V	0.0 V	0.0 V
12/ 27	9	IFOUT	J	2.2 V	2.2 V	2.2 V
13/ 26	10	ĪFOUT	12 (9)	2.2V	2.2 V	2.2 V
14/ 25	11	PLLGND	PLL ground	0.0 V	0.0 V	0.0 V
15/ 24	12	VT		VT	VT	VT
16/ 23	14	СР	15 (12	2.0 V	2.0 V	2.0 V
	13, 40	GND	ground	0.0 V	0.0 V	0.0 V



Table	Table 3-1 Pin Definition and Function (continued)							
Pin No.	Pin No	Symbol	Equivalent I/O-Schematic		Average DC voltage			
110.	140			LOW	MID	HIGH		
17/ 22	15	P4/ADC	17 (15)	5 V or V _{CE}	5 V or V _{CE}	5 V or V _{CE}		
18/ 21	16	XTAL	18 (16)	1.7 V	1.7 V	1.7 V		
19/ 20	17	XTAL		1.7 V	1.7 V	1.7 V		
20/ 19	18	P3		0 V or V _{CC} - V _{CE}	0 V or V _{CC} - V _{CE}	0 V or V _{CC} - V _{CE}		
21/ 18	19	P0	20 (18) or 21 (19) or 22 (20)	V _{CC} - V _{CE}	n.a.	n.a.		
22/ 17	20	P1		n.a.	V _{CC} - V _{CE}	n.a.		



Table	Table 3-1 Pin Definition and Function (continued)						
Pin No.	Pin No	Symbol	Equivalent I/O-Schematic	Avera	age DC vo	oltage	
				LOW	MID	HIGH	
23/ 16	21	AS	23 (21)	n.a.	n.a.	n.a.	
24/ 15	22	SCL	24 (22)	n.a.	n.a.	n.a.	
25/ 14	23	SDA	25 (23)	n.a	n.a	n.a	
26/ 13	26	GND	ground	0.0	0.0	0.0	



Table	Table 3-1 Pin Definition and Function (continued)							
Pin	Pin	Symbol	Equivalent I/O-Schematic	age DC vo	ige DC voltage			
No.	No			1.014	MID	111011		
07/	0.4	100		LOW	MID	HIGH		
27/ 12	24	AGC	27 (24)	3.5 V	3.5 V	3.5 V		
28/ 11	25	P2	28 (26)	n.a.	n.a.	0 V or V _{CC} - V _{CE}		
29/ 10	27	ĪFIN	29 30	n.a.	n.a.	n.a.		
30/ 9	28	IFIN	29 (27) (28)	n.a.	n.a.	n.a.		
31/ 8	29	MIXOUT	<u> </u>	4.0 V	4.0 V	4.0 V		
32/ 7	30	MIXOUT	31 (29) 32 (30) Oscillator	4.0 V	4.0 V	4.0 V		
33/ 6	31	RFGND	IF ground	0.0 V	0.0 V	0.0 V		

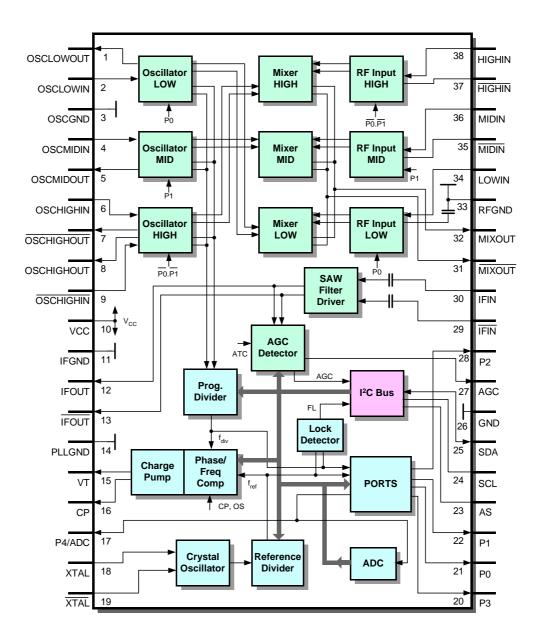


Table	Table 3-1 Pin Definition and Function (continued)						
Pin No.	Pin No	Symbol	Equivalent I/O-Schematic	Average DC volta		oltage	
				LOW	MID	HIGH	
34/ 5	32	LOWIN	34 (32)	1.9 V			
35/ 4	33	MIDIN	35 (33)		0.75 V		
36/ 3	34	MIDIN			0.75 V		
37/ 2	35	HIGHIN				0.75 V	
38/ 1	36	HIGHIN	37 (35)			0.75 V	



3.3 Block Diagram

3.3.1 TUA6034 in TSSOP-38 Package



TUA6034 BlockDiag TSSOP

Figure 3-4 Block Diagram TUA6034 in TSSOP-38 Package

3.3.2 TUA6036 in TSSOP-38 Package

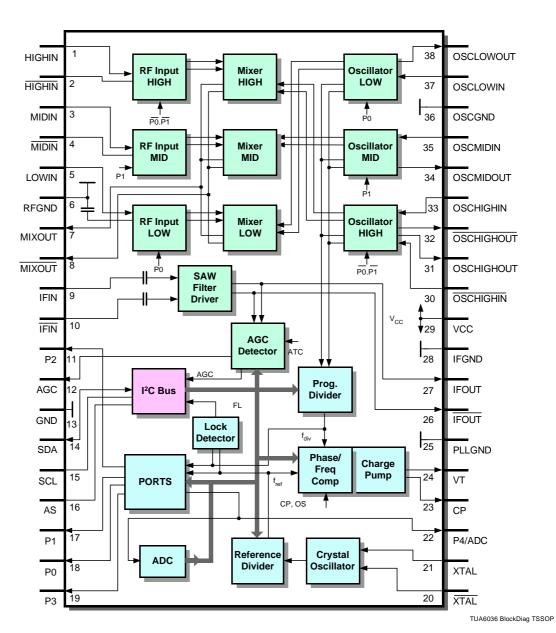
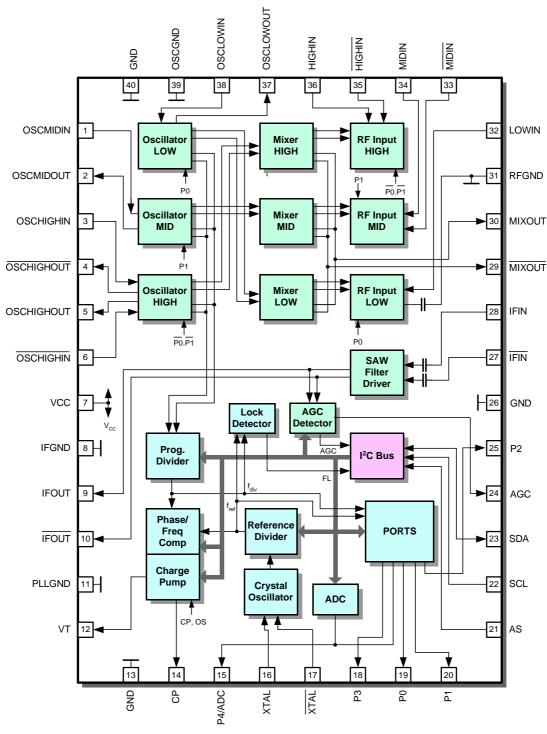


Figure 3-5 Block Diagram TUA6036 in TSSOP-38 Package



3.3.3 TUA6034 in VQFN-40 Package



TUA6034 Blockdiag VQFN

Figure 3-6 Block Diagram TUA6034 VQFN-40 Package

3.4 Circuit Description

3.4.1 Mixer-Oscillator block

The mixer-oscillator block includes three balanced mixers (one mixer with an unbalanced high-impedance input and two mixers with a balanced low-impedance input), two 2-pin asymmetrical oscillators for the LOW and the MID band, one 4-pin symmetrical oscillator for the HIGH band, an IF amplifier, a reference voltage, and a band switch.

Filters between tuner input and IC separate the TV frequency signals into three bands. The band switching in the tuner front-end is done by using three PNP port outputs. In the selected band the signal passes a tuner input stage with a MOSFET amplifier, a double-tuned bandpass filter and is then fed to the mixer input of the IC which has in case of LOW band a high-impedance input and in case of MID or HIGH band a low-impedance input. The input signal is mixed there with the signal from the activated on chip oscillator to the IF frequency. The IF is filtered by means of an IF filter in between the 2 mixer output pins and the 2 input pins of the following IF amplifier. The IF amplifier has a low output impedance to drive the SAW filter directly.

3.4.2 PLL block

The oscillator signal is internally DC-coupled as a differential signal to the programmable divider inputs. The signal subsequently passes through a programmable divider with ratio N = 256 through 32767 and is then compared in a digital frequency/phase detector with a reference frequency f_{ref} = 31.25, 50, 62.5, 125, 142.86 or 166.67 kHz. This frequency is derived from a balanced, low-impedance 4 MHz crystal oscillator (pins XTAL, $\overline{\text{XTAL}}$) divided by 128, 80, 64, 32, 28 or 24. The reference frequencies will be different with a quartz other than 4 MHz.

The phase detector has two outputs which drive four current sources of a charge pump. If the negative edge of the divided VCO signal appears prior to the negative edge of the reference signal, the positive current source pulses for the duration of the phase difference. In the reverse case the negative current source pulses. If the two signals are in phase, the charge pump output (CP) goes into the high-impedance state (PLL is locked). An active low-pass filter integrates the current pulses to generate the tuning voltage for the VCO (internal amplifier, external pull-up resistor at VT and external RC circuitry). The charge pump output is also switched into the high-impedance state if the control bits T2, T1, T0 = 0, 1, 0. Here it should be noted, however, that the tuning voltage can alter over a long period in the high impedance state as a result of self discharge in the peripheral circuity. VT may be switched off by the control bit OS to allow external adjustments.

If the VCO is not oscillating the PLL locks to a tuning voltage of 33V (V_{TH}).

By means of control bits CP, T0, T1 and T2 the pump current can be switched between four values by software. This programmability permits alteration of the control response of the PLL in the locked-in state. In this way different VCO gains can be compensated, for example.

The software controlled ports P0 to P4 are general purpose open-collector outputs. The test bits T2, T1, T0 =1, 0, 0 switch the test signals f_{div} (divided input signal) and f_{ref} (i.e.4 MHz / 64) to P0 and P1 respectively.

The lock detector resets the lock flag FL if the width of the charge pump current pulses is greater than the period of the crystal oscillator (i.e. 250 ns). Hence, if FL = 1, the maximum deviation of the input frequency from the programmed frequency is given by

$$\Delta f = \pm I_P * (K_{VCO} / f_{XTAL}) * (C1+C2) / (C1*C2)$$

where I_P is the charge pump current, K_{VCO} the VCO gain, f_{Xtal} the crystal oscillator frequency and C_1 , C_2 the capacitances in the loop filter (see Chapter 4). As the charge pump pulses at i.e. 62.5 kHz (= f_{ref}), it takes a maximum of 16 μ s for FL to be reset after the loop has lost lock state.

Once FL has been reset, it is set only if the charge pump pulse width is less than 250 ns for eight consecutive f_{ref} periods. Therefore it takes between 128 and 144 μs for FL to be set after the loop regains lock.

3.4.3 AGC

The wide band AGC stage detects the level of the IF output signal and generates an AGC voltage for gain control of the tuners input transistors. The AGC take-over and the time constant are selectable by the I²C bus.

3.4.4 I²C-Bus Interface

Data is exchanged between the processor and the PLL via the I^2C bus. The clock is generated by the processor (input SCL). Pin SDA functions as an input or output depending on the direction of the data (open collector, external pull-up resistor). Both inputs have a hysteresis and a low-pass characteristic, which enhance the noise immunity of the I^2C bus.

The data from the processor pass through an I²C bus controller. Depending on their function the data are subsequently stored in registers. If the bus is free, both lines will be in the marking state (SDA, SCL are high). Each telegram begins with the start condition and ends with the stop condition. Start condition: SDA goes low, while SCL remains high. Stop condition: SDA goes high while



SCL remains high. All further information transfer takes place during SCL = low, and the data is forwarded to the control logic on the positive clock edge.

The table 'Bit Allocation' (see Table 5-4 Bit Allocation Read / Write on page 46) should be referred to for the following description. All telegrams are transmitted byte-by-byte, followed by a ninth clock pulse, during which the control logic returns the SDA line to low (acknowledge condition). The first byte is comprised of seven address bits. These are used by the processor to select the PLL from several peripheral components (address select). The LSB bit (R/W) determines whether data are written into (R/W = 0) or read from (R/W = 1) the PLL.

In the data portion of the telegram during a WRITE operation, the MSB bit of the first or third data byte determines whether a divider ratio or control information is to follow. In each case the second byte of the same data type has to follow the first byte. Appropriate setting of the test bits will decide whether the band-switch byte or the auxiliary byte will be transmitted (see Table 5-7 Test modes on page 47).

If the address byte indicates a READ operation, the PLL generates an acknowledge and then shifts out the status byte onto the SDA line. If the processor generates an acknowledge, a further status byte is output; otherwise the data line is released to allow the processor to generate a stop condition. The status word consists of three bits from the A/D converter, the lock flag and the power-on flag.

Four different chip addresses can be set by an appropriate DC level at pin AS (see Table 5-6 Address selection on page 47).

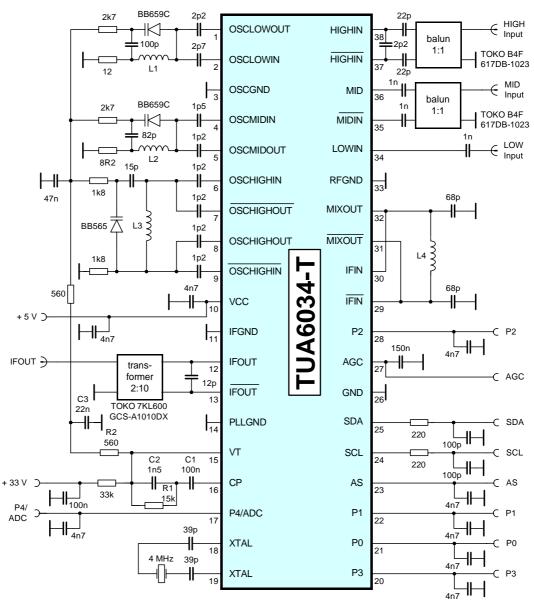
While the supply voltage is applied, a power-on reset circuit prevents the PLL from setting the SDA line to low, which would block the bus. The power-on reset flag POR is set at power-on and if V_{CC} falls below 3.2 V. It will be reset at the end of a READ operation.

4 Applications

Contents of this Chapter					
4.1	Circuits				
4-1	Application Circuit for ATSC				
4-2	Application Circuit for DVB-T				

Applications

4.1 Circuits



App Circuit ATSC

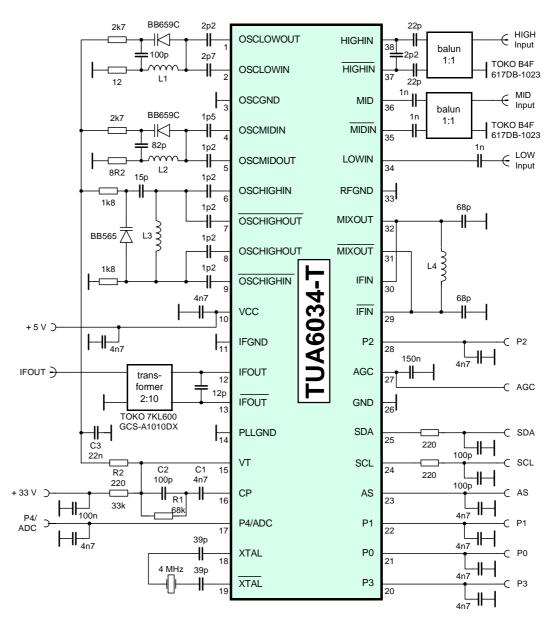
Figure 4-1 Application Circuit for ATSC

Remark: TUA 6036 has reversed pinning.

Rec	Recommended band limits in MHz						
	RF input		Oscillator				
	min	max	min	max			
LOW	55.25	157.25	101	203			
MID	163.25	451.25	201	479			
HIGH	457.25	861.25	503	907			

Coils						
	turns	diam.	wire diam.			
L1	8.5	3.2 mm	0.5 mm			
L2	2.5	3 mm	0.5 mm			
L3	1.5	2.4 mm	0.5 mm			
L4	12.5	3.5 mm	0.3 mm			

Applications



App Circuit DVBT

Figure 4-2 Application Circuit for DVB-T

Remark: TUA 6036 has reversed pinning.

Recommended band limits in MHz									
	RF input Oscillator								
	min	max	min	max					
LOW	48.25	154.25	87.15	193.15					
MID	161.25	439.25	200.15	478.15					
HIGH	447.25	863.25	486.15	902.15					

	Coils									
	turns	turns diam.								
L1	8.5	3.2 mm	0.5 mm							
L2	2.5	3 mm	0.5 mm							
L3	1.5	2.4 mm	0.5 mm							
L4	14.5	4 mm	0.3 mm							

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5.1 Electrical Data

5.1.1 Absolute Maximum Ratings



WARNING

The maximum ratings may not be exceeded under any circumstances, not even momentarily and individually, as permanent damage to the IC may result.

Table 5-1 Absolute Maximum Rat	ings				
Parameter ^{1).}	Symbol	Limit V	alues	Unit	Remarks
		min	max		
Supply voltage	V _{CC}	-0.3	6	V	
Ambient temperature	T _A	-40	T _{Amax} 2).	°C	
Junction temperature	TJ		+125	°C	
Storage temperature	T _{Stg}	-40	+125	°C	
Temperature difference junction to case ^{3).}	T _{JC}		2	K	
PLL			_		
СР	V _{CP}	-0.3	3	V	
	I _{CP}		1	mA	
Crystal oscillator pin XTAL	V _Q		6	V	
	IQ	-5		mA	
Bus input/output SDA	V _{SDA}	-0.3	6	V	
Bus output current SDA	I _{SDA(L)}		10	mA	open collector
Bus input SCL	V _{SCL}	-0.3	6	V	
Chip address switch AS	V _{AS}	-0.3	6	V	
VCO tuning output (loop filter)	V _{VT}	-0.3	35	V	
NPN port output voltage of P4	V _{P4}	-0.3	6	V	open collector
NPN port output current of P4	I _{P4(L)}	-1	10	mA	open collector, t _{max} = 0.1 sec. at 5.5 V



Table 5-1 Absolute Maximum Rat	ings (continued)			
Parameter*	Symbol	Limit V	alues	Unit	Remarks
		min	max		
P4/ADC input/output voltage	V _{P4/ADC}	-0.3	6	V	
NPN port output current of P4	I _{P4/ADC(L)}	-1	10	mA	open collector, t _{max} = 0.1 sec. at 5.5 V
PNP port output voltage of P0, P1, P2, P3	V _{P0, 1, 2, 3}	-0.3	6	V	open collector
PNP port output current of P1	I _{P1(L)}	+1	-25	mA	open collector, t _{max} = 0.1 sec. at 5.5 V
PNP port output current of P0	I _{P0(L)}	+1	-10	mA	open collector, t _{max} = 0.1 sec. at 5.5 V
PNP port output current of P2, P3	I _{P2, 3(L)}	+1	-5	mA	open collector, t _{max} = 0.1 sec. at 5.5 V
Total port output current of PNP ports	$\Sigma I_{P(L)}$		-40	mA	t _{max} = 0.1 sec. at 5.5 V
Mixer-Oscillator					
Mix inputs LOW band	V_{LOW}	-0.3	3	V	
Mix inputs MID/HIGH band	V _{MID/HIGH}		2	V	
	I _{MID/HIGH}	-5	6	mA	
VCO base voltage	V _B	-0.3	3	V	LOW, MID and HIGH band oscillators
VCO collector voltage	V _C		6	V	LOW, MID and HIGH band oscillators
ESD-Protection ^{4).}					
all pins	V _{ESD}		2	kV	

^{1).} All values are referred to ground (pin), unless stated otherwise. Currents with a positive sign flow into the pin and currents with a negative sign flow out of pin.

- 2). The maximum ambient temperature depends on the mounting conditions of the package. Any application mounting must guarantee not to exceed the maximum junction temperature of 125 °C. As reference the temperature difference junction to case is given.
- 3). Referred to top center of package.
- 4). According to EIA/JESD22-A114-B (HBM incircuit test), as a single device incircuit contact discharge test.

5.1.2 Operating Range

Within the operational range the IC operates as described in the circuit description. The AC / DC characteristic limits are not guaranteed.

Table 5-2 Operating Range							
Parameter	Symbol	Limit Values		Unit	Test Conditions	L	Item
		min	max				
Supply voltage	V _{CC}	+4.5	+5.5	V			
Programmable divider factor	N	256	32767				
LOW mixer input frequency range	f _{MIXV}	30	200	MHz			
MID and HIGH band mixer input frequency range	f _{MIXU}	130	900	MHz			
LOW oscillator frequency range	f _{OH}	65	250	MHz			
MID band oscillator frequency range	f _{OU}	165	530	MHz			
HIGH band oscillator frequency range	f _{OU}	400	950	MHz			
Ambient temperature	T _A	-20	T _{Amax}	°C			

^{1).} see 5.1.1 Absolute Maximum Ratings on page 32.

5.1.3 AC/DC Characteristics

Table 5-3 AC/DC Charac	teristics with	n T _A = 25 °	C, V _{CC} =	5 V				
	Symbol	L	imit Value	s	Unit	Test Conditions	L	Item
		min	typ	max				
Supply								
Supply voltage	V _{CC}	4.5	5	5.5	V			
Current consumption in	I _{VCC}	59	74	89	mA	LOW band		
active mode	I _{VCC}	59	74	89	mA	MID band		
	I _{VCC}	57	71	85	mA	HIGH band		
Current consumption in stand-by mode			20		mA	P0, P1 = 1		
Digital Part								
PLL								
Crystal oscillator connec	tions XTAL							
Crystal frequency	f _{XTAL}	3.2	4.0	4.8	MHz	series resonance		
Crystal resistance	R _Q		30	300	Ω	series resonance		
Input impedance	Z _Q	500	650		Ω	f _{XTAL} = 4 MHz		
Charge pump output CP								
Output current,	ICPDH	± 430	± 650	± 860	μΑ	VCP = 1.8 V		
see Table 5-11 Charge pump current on page 48	ICPH	± 180	± 250	± 360	μΑ	VCP = 1.8 V		
1. 1. 1. 1. 1. 1. 1. 2.	ICPDL	± 90	± 125	± 180	μA	VCP = 1.8 V		
	ICPL	± 35	± 50	± 70	μA	VCP = 1.8 V		
Tristate current	I _{CPZ}		± 1		nA	T2, T1, T0 = 0, 1, 0, V _{CP} = 2 V		
Output voltage	V _{CP}	1.0		2.5	V	loop locked		
Tuning voltage output VT	(open colle	ctor)						
Leakage current	I _{TH}			10	μA	V _{TH} = 33 V, OS = 1		
Output voltage when the loop is closed, (test mode in normal operation)	V _{TL}	0.4		32.7	V	OS=0, $R_{Load} = 33 \text{ k}\Omega$, tuning supply = 33 V		
I ² C-Bus								
Bus inputs SCL, SDA								
High-level input voltage	V _{IH}	2.3		5.5	V			
Low-level input voltage	V _{IL}	0		1.5	V			



Table 5-3 AC/DC Charac			imit Value			Test Conditions	,	140.00
	Symbol	min L	typ	es max	Unit	lest Conditions	L	Item
High-level input current	I _{IH}	111111	цр	10	μA	$V_{bus} = 5.5 \text{ V},$ $V_{CC} = 0 \text{ V}$		
	I _{IH}			10	μA	$V_{bus} = 5.5 \text{ V},$ $V_{CC} = 5.5 \text{ V}$		
Low-level input current	I _{IL}			10	μA	$V_{bus} = 1.5 \text{ V},$ $V_{CC} = 0 \text{ V}$		
	I _{IL}	-10			μA	$V_{bus} = 0 V,$ $V_{CC} = 5.5 V$		
Bus output SDA (open co	ollector)							
Leakage current	I _{OH}			10	μΑ	V _{OH} = 5.5 V		
Low-level output voltage	V _{OL}			0.4	V	I _{OL} = 3 mA		l
Edge speed SCL,SDA								
Rise time	t _r			300	ns			
Fall time	tf			300	ns			
Clock timing SCL								
Frequency	f _{SCL}	0	100	400	kHz			
High pulse width	t _H	0.6			μs			
Low pulse width	tL	1.3			μs			
Start condition								
Set-up time	t _{susta}	0.6			μs			
Hold time	t _{hsta}	0.6			μs			
Stop condition								
Set up time	t _{susto}	0.6			μs			
Bus free	t _{buf}	1.3			μs			
Data transfer								
Set-up time	t _{sudat}	0.1			μs			
Hold time	t _{hdat}	0			μs			
Input hysteresis SCL, SDA	V _{hys}		200		mV			
Pulse width of spikes which are suppressed	t _{sp}	0		50	ns			
Capacitive load for each bus line	C _L			400	pF			



Table 5-3 AC/DC Charac	Symbol		imit Value		Unit	Test Conditions	L	Iten
	Syllibol	min			Offic	rest Conditions	_	iteii
PNP port outputs P0, P1,	P2 P3 (one)		typ	max				
Port output voltage		Conecto	0.05	0.4	V	I 0 mΛ		
Fort output voitage	V _{POH0to3}		0.03	0.4	V	I _{POLH0to3} = 0 mA, port disabled		
Output saturation voltage port 0	$V_{PL0} = V_{CC} - V_{CESat0}$		0.25	0.4	V	I _{POL0} = 10 mA, port enabled		
Output saturation voltage port 1	V _{PL1} = V _{CC} - V _{CESat1}		0.25	0.4	V	I _{POL1} = 15 mA port enabled		
Output saturation voltage ports 2, 3	$V_{PL2,3} = V_{CC} - V_{CESat2,3}$		0.25	0.4	V	I _{POL2, 3} = 5 mA port enabled		
NPN port output P4 (oper	n collector)							
Output leakage current	I _{POH4}			10	μA	$V_{CC} = 5.5,$ $V_{Pn4} = 6 \text{ V}$		
Output saturation voltage	V _{PL04}		0.25	0.4	V	I _{POL4} = 5 mA		
ADC input								
ADC input voltage	V_{ADC}	0		5.5	V			
High-level input current	I _{ADCH}			10	μA			
Low-level input current	I _{ADCL}	-10			μA			
Address selection input A	AS							
High-level input current	I _{ASH}			50	μΑ	V _{ASH} = 5.5 V		
Low-level input current	I _{ASL}	-50			μA	V _{ASL} = 0 V		
Analog Part								
LOW band mixer mode (F	P0 = 1, P1 =0	, including	ıF ampli	fier)				
RF frequency	f _{RF}	44.25		170.25	MHz	picture carrier ^{1).}		_
Voltage gain	G _V	23.5	26	28.5	dB	f _{RF} = 44.25 MHz, see 5.5.1 on page 54		
	G _V	23.5	26	28.5	dB	f _{RF} = 170.25 MHz, see 5.5.1 on page 54		
Noise figure	NF		8	10	dB	f _{RF} = 50 MHz, see 5.5.4 on page 55, see 5.5.3 on page 55		
	NF		8	10	dB	f _{RF} = 150 MHz, see 5.5.4 on page 55, see 5.5.3 on page 55		



Table 5-3 AC/DC Charac	teristics with	n T _A = 25 °	C, V _{CC} =	5 V (conti	nued)			
	Symbol	L	imit Value	es	Unit	Test Conditions	L	Item
		min	typ	max				
Output voltage causing 0.8% of crossmodulation	V _O		113		dΒμV	f _{RF} = 48.25 MHz, see 5.5.6 on page 56		
in channel	V _O		113		dΒμV	f _{RF} = 154.25 MHz, see 5.5.6 on page 56		
Input IP2	IIP2		160		dΒμV	fRF1 = 48.25 MHz fRF2 = 97.50 MHz, PRF1 = PRF2		
	IIP2		145		dΒμV	fRF1 = 154.25 MHz fRF2 = 309.50 MHz, PRF1 = PRF2		
Input IP3	IIP3		118		dΒμV	fRF1 = 48.25 MHz fRF2 = 49.25 MHz PRF1 = PRF2		
	IIP3		117		dΒμV	fRF1 = 154.25 MHz fRF2 = 155.25 MHz, PRF1 = PRF2		
Output voltage causing 1 dB compression	Vo		124		dΒμV	fRF = 48.25 MHz		
	Vo		124		dΒμV	fRF = 154.25 MHz		
Output voltage causing 1.1 kHz incidental FM	V _O	108	111		dBµV	f _{RF} = 48.25 MHz ^{2).}		
1.1 KHZ IIICIQEIIIAI FIVI	V _O	108	111		dΒμV	f _{RF} = 154.25 MHz ^{2.)}		
Local oscillator FM caused by I ² C communication	FM _{I2C}			2.12	kHz	f _{RF} = 154.25 MHz ^{3).}		
750 Hz Pulling	V _i	88			dΒμV	f _{RF} = 154.25 MHz ^{4).}		
Channel S02 beat	INT _{S02}	57	60		dBc	V _{RFpix} = 115 dBμV at IF output ^{5).}		
Channel A-5 beat	INT _{A-5}	57	60		dBc	V _{RFpix} = 115 dBμV at IF output ^{6).}		
Channel CH6 color beat	INT _{CH6}	63	66		dBc	$V_{RFpix} = 80 \text{ dB}\mu\text{V}$ $V_{RFsnd} = 80 \text{ dB}\mu\text{V}^{7)}$.		
RF input level without lock-out	V _i			120	dΒμV	8).		
Input conductance	g _i		0.15		mS	f _{RF} = 48.25 MHz, see 5.4.1 on page 51		
	g _i		0.15		mS	f _{RF} = 154.25 MHz, see 5.4.1 on page 51		
Input capacitance	C _{MixV}		1		pF	f _{RF} = 48.25 to 154.25 MHz, see 5.4.1 on page 51		



Table 5-3 AC/DC Charac	teristics with	n T _A = 25 °	C, V _{CC} = !	5 V (conti	nued)			
	Symbol	L	imit Value	es	Unit	Test Conditions	L	Item
		min	typ	max				
Mid band mixer mode (PC			IF amplific	-				
RF frequency	f _{RF}	154.25		454.25	MHz	picture carrier ^{1.)}		
Voltage gain	G _V	33	36	39	dB	f _{RF} = 161.25 MHz, see 5.5.2 on page 54		
	G _V	33	36	39	dB	f _{RF} = 439.25 MHz, see 5.5.2 on page 54		
Noise figure (not corrected for image)	NF		6	8	dB	f _{RF} = 161.25 MHz, see 5.5.5 on page 56		
	NF		6	8	dB	f _{RF} = 300 MHz, see 5.5.5 on page 56		
Output voltage causing 0.8% of crossmodulation	V _O		112		dΒμV	f _{RF} = 161.25 MHz, see 5.5.7 on page 57		
in channel	V _O		112		dΒμV	f _{RF} = 439.25 MHz, see 5.5.7 on page 57		
Input IP2	IIP2		146		dΒμV	fRF1 = 161.25 MHz fRF2 = 323.50 MHz, PRF1 = PRF2		
	IIP2		140		dΒμV	fRF1 = 440.25 MHz fRF2 = 818.50 MHz, PRF1 = PRF2		
Input IP3	IIP3		105		dΒμV	fRF1 =161.25 MHz fRF2 = 162.25 MHz PRF1 = PRF2		
	IIP3		106		dΒμV	ffRF1 =439.25 MHz fRF2 = 440.25 MHz PRF1 = PRF2		
Output voltage causing	V _o		124		dΒμV	fRF = 161.25 MHz		
1 dB compression	Vo		124		dΒμV	fRF =439.25 MHz		
Output voltage causing 1.1 kHz incidental FM	Vo	108	111		dΒμV	f _{RF} = 161.25 MHz ^{2.)}		
1.1 KHZ IIICIGEHIGIT W	V _O	108	111		dΒμV	f _{RF} = 439.25 MHz ^{2.)}		
Local oscillator FM caused by I ² C communication	FM _{I2C}			2.12	kHz	f _{RF} = 439.25 MHz ^{3.)}		
N+5 - 1 MHz pulling	N+5 - 1 MHz	77	80		dΒμV	f_{RFw} = 359.25 MHz, f_{OSC} = 398.15 MHz, f_{RFu} = 399.25 MHz ^{9).}		
750 Hz Pulling	V _i	78			dΒμV	f _{RF} = 439.25 MHz ^{4.)}		
RF input level without lock-out	V _i			120	dΒμV	8.)		



Table 5-3 AC/DC Charact	teristics with	n T _A = 25 °	C, V _{CC} = 5	5 V (conti	nued)			
	Symbol	L	imit Value	es	Unit	Test Conditions	L	ltem
		min	typ	max				
Input impedance $Z_i = (R_s + j\omega L_s)$	R _s		35		Ω	f _{RF} = 161.25.25 MHz, see 5.4.2 on page 51		
	R _s		35		Ω	f _{RF} = 439.25 MHz, see 5.4.2 on page 51		
	L _s		8		nH	f _{RF} = 161.25.25 MHz, see 5.4.2 on page 51		
	L _s		8		nH	f _{RF} = 439.25 MHz, see 5.4.2 on page 51		
HIGH band mixer mode (F	P0 = 0, P1 = 0), includin	g IF ampl	ifier)				
RF frequency	f _{RF}	399.25		863.25	MHz	picture carrier 1.)		
Voltage gain	G _V	33	36	39	dB	f _{RF} = 447.25 MHz, see 5.5.2 on page 54		
	G _V	33	36	39	dB	f _{RF} = 863.25 MHz, see 5.5.2 on page 54		
Noise figure (not corrected for image)	NF		6	8	dB	f _{RF} = 447.25 MHz, see 5.5.5 on page 56		
	NF		7	9	dB	f _{RF} = 863.25 MHz, see 5.5.5 on page 56		
Output voltage causing 0.8% of crossmodulation	V _O		112		dΒμV	f _{RF} = 447.25 MHz, see 5.5.7 on page 57		
in channel	V _O		112		dΒμV	f _{RF} = 863.25 MHz, see 5.5.7 on page 57		
Input IP2	IIP2		136		dΒμV	fRF1 = 447.25 MHz fRF2 = 895.50 MHz, PRF1 = PRF2		
Input IP3	IIP3		106		dΒμV	fRF1 = 447.25 MHz fRF2 = 448.25 MHz PRF1 = PRF2		
	IIP3		106		dΒμV	fRF1 = 863.25 MHz fRF2 = 864.25 MHz PRF1 = PRF2		
Output voltage causing	Vo		124		dΒμV	fRF = 447.25 MHz		
1 dB compression	V _o		124		dΒμV	fRF = 863.25 MHz		
Output voltage causing 1.1 kHz incidental FM	V _O	108	111		dΒμV	f _{RF} = 447.25 MHz ^{2.)}		
Wiz mordonari w	V _O	108	111		dΒμV	f _{RF} = 454.25 MHz ^{2.)}		
Local oscillator FM caused by I ² C communication	FM _{I2C}			2.12	kHz	f _{RF} = 863.25 MHz ^{3.)}		



	Symbol	L	imit Value	s	Unit	Test Conditions	L	Item
		min	typ	max				
N+5 - 1 MHz pulling	N+5 - 1 MHz	77	80		dΒμV	$f_{RFw} = 823.25 \text{ MHz},$ $f_{OSC} = 862.15 \text{ MHz},$ $f_{RFu} = 862.25 \text{ MHz}$ ^{9.)}		
750 Hz Pulling	V _i	78			dΒμV	f _{RF} = 855.25 MHz ^{4.)}		
RF input level without lock-out	V _i			120	dΒμV	8.)		
Input impedance $Z_i = (R_s + j\omega L_s)$	R _s		35		Ω	f _{RF} = 407.25 MHz, see 5.4.3 on page 52		
	R _s		35		Ω	f _{RF} = 863.25 MHz, see 5.4.3 on page 52		
	L _s		8		nH	f _{RF} = 407.25 MHz, see 5.4.3 on page 52		
	L _s		8		nH	f _{RF} = 863.25 MHz, see 5.4.3 on page 52		
LOW band oscillator, see	Chapter 4							
Oscillator frequency	fosc	80		210	MHz	10).		
Oscillator frequency shift	$\Delta f_{OSC(V)}$		20	70	kHz	$\Delta V_{CC} = 5\% ^{11)}$.		
	$\Delta f_{OSC(V)}$		110		kHz	$\Delta V_{CC} = 10\% ^{11.)}$		
Oscillator frequency drift	$\Delta f_{OSC(T)}$		300	500	kHz	$\Delta T = 25$ °C, with compensation 12).		
Oscillator frequency drift	$\Delta f_{OSC(t)}$		150	250	kHz	5 s to 15 min after switch on ^{13).}		
Phase noise, carrier to noise sideband	$\Phi_{\sf OSC}$	77 ^{14).}	85		dBc/ Hz	±1 kHz frequency off- set, worst case in fre- quency range		
		88 ^{15).}	92		dBc/ Hz	±10 kHz frequency offset, worst case in frequency range		
		108 14), 15)	112		dBc/ Hz	±100 kHz frequency offset, worst case in frequency range		
Ripple susceptibility of V _P	RSC	15	20		mV	4.75 V < VP < 5.25 V, worst case in frequency range, ripple frequency 500 kHz 16).		
MID band oscillator, see (Chapter 4							
Oscillator frequency	fosc	201		493	MHz	10.)		



Min	typ 20 110	es max 70	Unit	Test Conditions	L	Item
min	20 110					
	110	70				
			kHz	$\Delta V_{CC} = 5\%^{11.)}$		
	500		kHz	$\Delta V_{CC} = 10\% ^{11.)}$		
	500	750	kHz	$\Delta T = 25$ °C; with compensation ^{12.)}		
	250	500	kHz	5 s to 15 min after switch on ^{13.)}		
73 ^{14.)}	80		dBc/ Hz	±1 kHz frequency off- set, worst case in fre- quency range		
88 ^{15.)}	92		dBc/ Hz	±10 kHz frequency offset, worst case in frequency range		
106 14), 15)	112		dBc/ Hz	±100 kHz frequency offset, worst case in frequency range		
15	20		mV	4.75 < VP < 5.25 V, worst case in fre- quency range, ripple frequency 500 kHz 14.)		
435		905	MHz	10.)		
	20	70	kHz	$\Delta V_{CC} = 5\% ^{11.)}$		
	300		kHz	$\Delta V_{CC} = 10\% ^{11.)}$		
	600	1000	kHz	$\Delta T = 25$ °C; with compensation ^{12.)}		
	250	500	kHz	5 s to 15 min after switch on ^{13).}		
70 ^{14.)}	77		dBc/ Hz	±1 kHz frequency off- set, worst case in fre- quency range		
86 ¹⁵⁾	90		dBc/ Hz	±10 kHz frequency offset, worst case in frequency range		
106 14), 15)	109		dBc/ Hz	±100 kHz frequency offset, worst case in frequency range		
15	20		mV	4.75 < VP < 5.25 V, worst case in fre- quency range, ripple frequency 500 kHz 14.)		
					frequency range 15 20 mV 4.75 < VP < 5.25 V, worst case in frequency range, ripple frequency 500 kHz	frequency range 15 20 mV 4.75 < VP < 5.25 V, worst case in frequency range, ripple frequency 500 kHz



Table 5-3 AC/DC Charac			imit Value			Took Conditions		14
	Symbol	min L	typ	max	Unit	Test Conditions	L	Item
Input impedance $Z_i = (R_s + j\omega L_s)$	R _S	111111	460	тах	Ω	at 36 MHz, see 5.4.4 on page 52		
, ,	L _S		10		nH	at 36 MHz, see 5.4.4 on page 52		
Output reflection coeffi- cient	S ₂₂		10		dB	magnitude, see 5.4.6 on page 53		
	S ₂₂		0.85		٥	phase, see 5.4.6 on page 53		
Output impedance $Z_0 = (R_s + j\omega L_s)$	R _S		65		Ω	at 36 MHz, see 5.4.6 on page 53		
	L _S		20		nH	at 36 MHz, see 5.4.6 on page 53		
Rejection at the IF output	s							
Level of divider interferences in the IF signal	INT _{DIV}			20	dΒμV	^{17).} , worst case		
Crystal oscillator interferences rejection	INT _{XTAL}	60	66		dBc	$V_{IF} = 100 \text{ dB}\mu\text{V},$ worst case in frequency range ^{18).}		
Reference frequency rejection	INT _{REF}	60	66		dBc	V _{IF} = 100 dBμV, worst case in fre- quency range ^{19).}		
AGC output								
AGC take-over point	AGC _{TOP}		112		dΒμV	AL2, AL1, AL0 = 0, 1, 0		
Source current 1	I _{AGCfast}	7.2	9.0	10.8	μΑ			
Source current 2	I _{AGCslow}	210	300	390	nA			
Peak sink to ground	I _{AGCpeak}	80	100	120	μΑ			
AGC output voltage	V _{AGCmax}	3.6	3.8	4.0	V	maximum level, I _{AGC} = 9 μA		
AGC output voltage	V _{AGCmin}	0		0.25	V	minimum level		
RF voltage range to switch the AGC from active to inactive mode	AGC _{SLIP}			0.5	dB			
AGC output voltage	AGC _{RML}	0		2.9	V	AGC bit high or AGC active		
AGC output voltage	AGC _{RMH}	3.3	3.8	VCC- 0.5 or 4	V	AGC bit low or AGC inactive		

Table 5-3 AC/DC Characteristics with T _A = 25 °C, V _{CC} = 5 V (continued)										
	Symbol	Limit Values		Unit	Test Conditions	L	Item			
		min	typ	max						
AGC leakage current	AGC _{LEAK}	-50		50	nA	AL2, AL1, AL0 = 1,1,0 0 < V _{AGC} < V _{CC}				
AGC output voltage	AGC _{OFF}	3.3	3.8	VCC- 0.5 or 4	V	AL2, AL1, AL0 = 1,1,1 AGC is disabled				

- This value is only guaranteed in lab.
 - 1). The RF frequency range is defined by the oscillator frequency range and the intermediate frequency (IF).
 - 2). This is the level of the RF unwanted signal (50% amplitude modulated with 1kHz) that causes a 1.1 kHz FM modulation of the local oscillator and thus of the wanted signal; $V_{wanted} = 100 \text{ dB}\mu\text{V}$; $f_{unwanted} = f_{wanted} + 5.5 \text{ MHz}$.
 - 3). Local oscillator FM modulation resulting from I^2C communication is measured at the IF output using a modulation analyser with a peak to peak detector (($P_+ + P_-$)/2) and a post detection filter 30 Hz 200 kHz. The I^2C messages are sent to the tuner in such a way that the tuner is addressed but the content of the PLL registers are not altered. The refresh interval between each data set shall be 20 ms to 1s.
 - 4). This is the level of the RF signal (100% amplitude modulated with 11.89 kHz) that causes a 750 Hz frequency deviation on the oscillator signal producing sidebands 30 dB below the level of the oscillator signal.
 - 5). Channel S02 beat is the interfering product of f_{RFpix} , f_{IF} and f_{OSC} of channel S02, f_{BEAT} = 37.35 MHz. The possible mechanisms are f_{OSC} 2 x f_{IF} or 2 x f_{RFpix} f_{OSC} .
 - 6). Channel A-5 beat is the interfering product of f_{RFpix} , f_{IF} and f_{OSC} of channel A-5; f_{BEAT} = 45.5 MHz. The possible mechanisms are: f_{OSC} 2 x f_{IF} or 2 x f_{RFpix} f_{OSC} .
 - 7). Channel 6 beat is the interfering product of f_{RFpix} + f_{RFsnd} f_{OSC} of channel 6 at 42 MHz.
 - 8). The IF output signal stays stable within the range of the f_{ref} step for a low level RF input up to 120 dBμV.
 - 9). N+5 -1 MHz is defined as the input level of channel N+5, at frequency 1 MHz lower, causing FM sidebands 30 dB below the wanted carrier.
 - 10). Limits are related to the tank circuit used in the application board (see Chapter 4). Frequency bands may be adjusted by the choice of external components.
 - 11). The frequency shift is defined as a change in oscillator frequency when the supply voltage varies from $V_{CC} = 5$ to 4.75 V (4.5 V) or from $V_{CC} = 5$ to 5.25 V (5.5 V). The oscillator is free running during this measurement.
 - 12). The frequency drift is defined as a change in oscillator frequency if the ambient temperature varies from $T_A = 25$ to 50 °C or from $T_A = 25$ to 0 °C. The oscillator is free running during this measurement.
 - 13). The switch-on drift is defined as a change in oscillator frequency between 5 s and 15 min after switch-on. The oscillator is free running during this measurement.
 - 14). see Figure 4-2 Application Circuit for DVB-T on page 30.
 - 15). see Figure 4-1 Application Circuit for ATSC on page 29.
 - 16). The supply ripple susceptibility is measured in the application board (see Chapter 4), using a spectrum analyser connected to the IF output. An unmodulated RF signal is applied to the test board RF input. A sinewave signal with a frequency of 500 kHz is superposed onto the supply voltage (see 5.5.8 on page 57). The amplitude of this ripple is adjusted to bring the 500 kHz sidebands around the IF carrier to a level of 53.5 dBc referred to the carrier.



- 17). This is the level of divider interferences close to the IF frequency. For example channel S3: $f_{OSC} = 158.15$ MHz, 1/4 $f_{OSC} = 39.5375$ MHz. Divider interference is measured with the application board (see Chapter 4). All ground pins are connected to a single ground plane under the IC. The LOWIN input must be left open (i.e. not connected to any load or cable). The MIDIN and HIGHIN inputs are connected to a hybrid. The measured level of divider interference are influenced by layout, grounding and port decoupling. The measurement results between various applications and the reference board could vary as much as 10 dB.
- 18). Crystal oscillator interference means the 4 MHz sidebands caused by the crystal oscillator. The rejection has to be greater than 60 dB for an IF output of 100 dB μ V.
- 19). The reference frequency rejection is the level of reference frequency sidebands (e.g. 62.5 kHz) related to the carrier. The rejection has to be greater than 60 dB for an IF output of 100 dB μ V.

5.2 Programming

Table 5-4 Bit Allocation Read / Write											
Name	Byte		Bits								
		MSB	bit6	bit5	bit4	bit3	bit2	bit1	LSB		
Write Data											
Address Byte	ADB	1	1	0	0	0	MA1	MA0	R/W=0	Α	
Divider Byte 1	DB1	0	N14	N13	N12	N11	N10	N9	N8	Α	
Divider Byte 2	DB2	N7	N6	N5	N4	N3	N2	N1	N0	Α	
Control byte	СВ	1	CP	T2	T1	T0	RSA	RSB	os	Α	
Bandswitch byte	BB				P4	P3	P2	P1	P0	Α	
Auxiliary byte 1).	AB	ATC	AL2	AL1	AL0	0	0	0	0	Α	
Read data											
Address byte	ADB	1	1	0	0	0	MA1	MA0	R/W=1	Α	
Status byte	SB	POR	FL	1	1	AGC	A2	A1	A0	Α	

^{1).} AB replaces BB when T2, T1, T0 = 0, 1, 1, see Table 5-7 Test modes on page 47.

Table 5-5 Description of S	Symbols
Symbol	Description
A	Acknowledge
MA0, MA1	Address selection bits, see Table 5-6 Address selection on page 47
N14 to N0	programmable divider bits: $N = 2^{14} \times N14 + 2^{13} \times N13 + + 2^{3} \times N3 + 2^{2} \times N2 + 2^{1} \times N1 + N0$
СР	charge pump current bit: bit = 0: charge pump current = 50 μA or 125 μA bit = 1: charge pump current = 250 μA (default) or 650 μA, see Table 5-11 Charge pump current on page 48
T0, T1, T2	test bits, see Table 5-7 Test modes on page 47
RSA, RSB	reference divider bits, see Table 5-8 Reference divider ratios on page 47
OS	tuning amplifier control bit: bit = 0: enable V_T bit = 1: disable V_T (default)
P0, P1, P2, P3	PNP ports control bits bit = 0: Port is inactive, high impedance state (default) bit = 1: Port is active, $V_{OUT} = V_{CC} - V_{CESAT}$
P4	NPN port control bit bit = 0: Port is inactive, high impedance state (default) bit = 1: Port is active, V _{OUT} = V _{CESAT}
ATC	AGC time constant bit bit = 0: I_{AGC} =300 nA; Δt =2s with C=160 nF (default) bit = 1: I_{AGC} =9 μ A; Δt =50ms with C=160 nF



Table 5-5 Description of S	Table 5-5 Description of Symbols							
AL0, AL1, AL2	GC take-over point bits, see Table 5-9 AGC take-over point on page 48							
POR	Power-on reset flag; POR =1 at power-on							
FL	PLL lock flag bit = 1: loop is locked							
AGC	internal AGC flag. AGC=1 when internal AGC is active (level below 3V)							
A0, A1, A2	digital output of the 5-level ADC							

Table 5-6 Address selection								
Voltage at AS	MA1	MA0						
(0 to 0.1) x V _{CC}	0	0						
open circuit or (0.2 to 0.3) x V _{CC}	0	1						
(0.4 to 0.6) x V _{CC}	1	0						
(0.9 to 1) x V _{CC}	1	1						

Table 5-7 Test modes			
Mode	T2	T1	T0
Normal mode, charge pump currents 50 and 250 µA selectable	0	0	0
Normal mode, charge pump currents 50 and 250 µA selectable (default)	0	0	1
CP is in high-impedance state	0	1	0
byte AB will follow (otherwise byte BB will follow)	0	1	1
$P0 = f_{div}$ output, $P1 = f_{ref}$ output	1	0	0
not in use	1	0	1
Extended mode, charge pump currents 50 and 250 µA selectable	1	1	0
Extended mode, charge pump currents 125 and 650 µA selectable	1	1	1

Table 5-8 Reference divider ratios							
Reference divider ratio	f _{ref} 1).	Mode	T2	T1	RSA	RSB	
80	50 kHz	normal	0	0	0	0	
128	31.25 kHz	normal	0	0	0	1	
24	166.67 kHz	Х	Х	Х	1	0	
64	62.5 kHz	Х	Х	Х	1	1	
32	125 kHz	extended	1	1	0	0	
28	142.86 kHz	extended	1	1	0	1	

^{1).} With a 4 MHz quartz.

Table 5-9 AGC take-over point						
IF output level, symmetrical mode	Remark	AL2	AL1	AL0		
115 dBµV		0	0	0		
115 dBµV		0	0	1		
112 dBµV	default mode at POR	0	1	0		
109 dBµV		0	1	1		
106 dBµV		1	0	0		
103 dBμV		1	0	1		
I _{AGC} = 0	External AGC 1).	1	1	0		
3.8 V	Disabled ^{2).}	1	1	1		

^{1).} The AGC detector is disabled. Both the sinking and sourcing current from the IC is disabled. The AGC output goes into a high impedance state and an external AGC source can be connected in parallel and will not be influenced.

2). The AGC detector is disabled and I_{AGC} = 9 $\mu A.$

Table 5-10 A to D converter levels ^{1).}							
Voltage at ADC	A2	A1	Α0				
(0 to 0.15) * V _{CC}	0	0	0				
(0.15 to 0.3) * V _{CC}	0	0	1				
(0.3 to 0.45) * V _{CC}	0	1	0				
(0.45 to 0.6) * V _{CC}	0	1	1				
(0.6 to 1) * V _{CC}	1	0	0				

^{1).} No erratic codes in the transition.

Table 5-11 Charge pump current						
Charge pump current	Mode	СР	T2	T1	T0	
50 μΑ		0	0	0	x ^{1).}	
250 μA (default)	normal	1	0	0	Х	
50 μA		0	1	1	0	
125 µA	extended	0			1	
250 μΑ		1			0	
650 μA		1			1	

^{1).} x = don't care.

Table 5-12 Internal band selection						
Band	Mixer	Oscillator				
LOW	P0. P1 ^{1).}	P0. P1				
MID	P1. P0	P1. P 0				
HIGH (default)	P0.P1	P0.P1				
Stand-by mode	P0, P1	P0, P1				

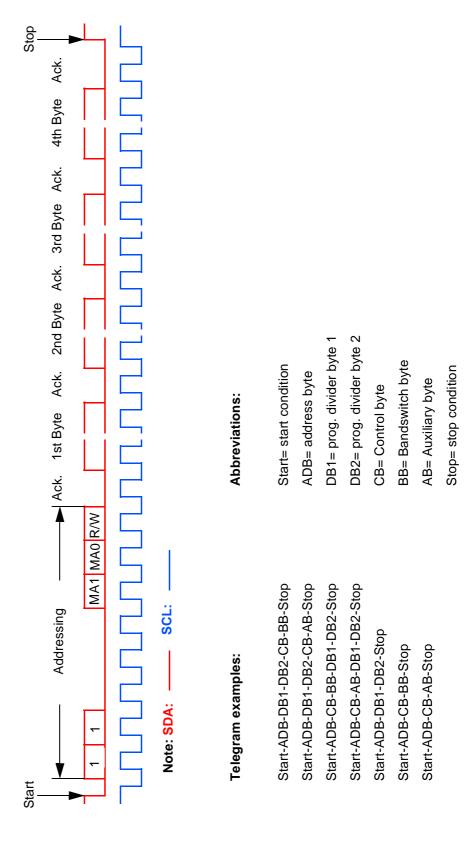
^{1).} Means: (P0 AND NOT P1); that is: LOW mixer is switched on if (P0=1 and P1=0).

Table 5-13 Defaults at power-on reset									
Name	Byte	Bits							
		MSB	bit6	bit5	bit4	bit3	bit2	bit1	LSB
Write Data									
Address Byte	ADB	1	1	0	0	0	MA1	MA0	R/W=0
Divider byte 1	DB1	0	x ^{1).}	х	×	х	×	х	x
Divider byte 2	DB2	х	х	х	х	х	х	х	х
Control byte	СВ	1	1	0	0	1	х	х	1
Bandswitch byte	ВВ	0	0	0	0	0	0	0	0
Auxiliary byte	AB	0	0	1	0				

^{1).} x = don't care.

Table 5-14 Description of modes							
Mode	Description						
normal	Reference divider ratios 24, 64, 80 , 128 selectable. Charge pump currents 50, 250 µA selectable. Auxiliary byte to follow Control byte (T2=0, T1=1, T0=1), otherwise Bandswitch byte to follow Control byte.						
extended	Reference divider ratios 24, 28 , 32 , 64 selectable. Charge pump currents 50, 125 , 250, 650 µA selectable. Auxiliary byte to follow Control byte (T2=0, T1=1, T0=1), otherwise Bandswitch byte to follow Control byte.						

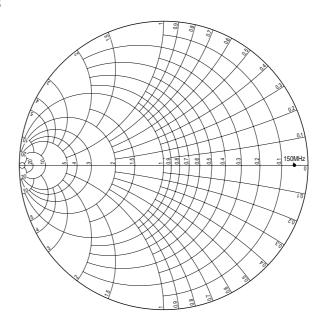
5.3 I²C Bus Timing Diagram



5.4 Electrical Diagrams

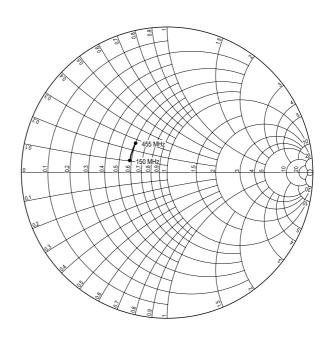
5.4.1 Input admittance (S11) of the LOW band mixer (40 to 150 MHz)

$$Y_0 = 20mS$$



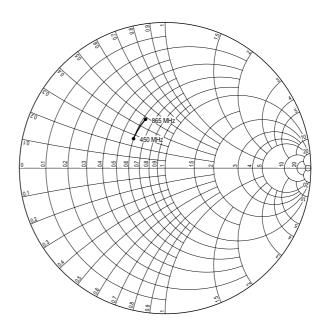
5.4.2 Input impedance (S11) of the MID band mixer (150 to 455 MHz)

$$Z_0 = 50~\Omega$$



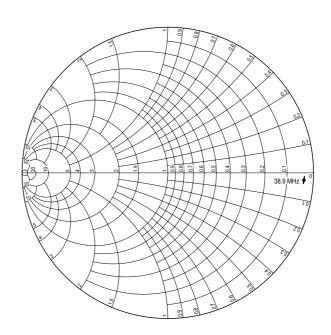
5.4.3 Input impedance (S11) of the HIGH band mixer (450 to 865 MHz)

$$Z_0 = 50 \Omega$$



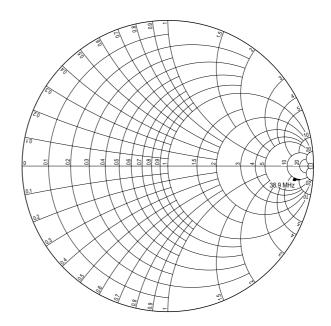
5.4.4 Output admittance (S22) of the of the mixers (30 to 50 MHz)

$$Y_0 = 20 ms$$



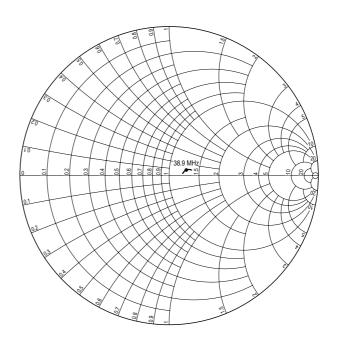
5.4.5 Input impedance (S11) of the IF amplifier (30 to 50 MHz)

$$Z_0 = 50 \Omega$$



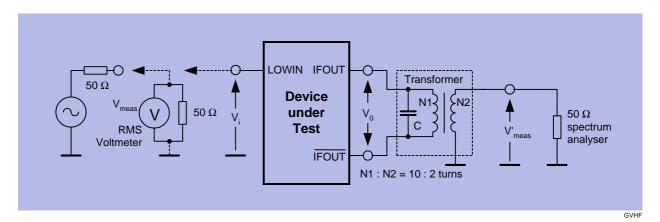
5.4.6 Output impedance (S22) of the IF amplifier (30 to 50 MHz)

$$Z_0 = 50 \Omega$$



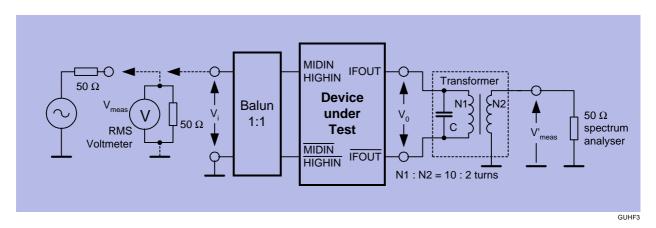
5.5 Measurement Circuits

5.5.1 Gain (G_V) measurement in LOW band



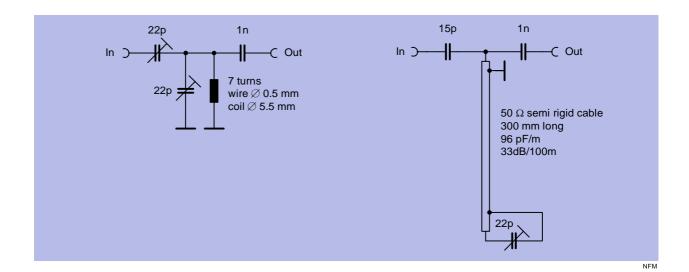
- $Z_i >> 50 Ω => V_i = 2 x V_{meas} = 80 dBμV$
- V_i = V_{meas} + 6dB = 80 dBµV
- V₀ = V'_{meas} + 16 dB (transformer ratio N1:N2 and transformer loss
- $G_v = 20 \log(V_0 / V_i)$

5.5.2 Gain (G_V) measurement in MID and HIGH bands



- V_i = V_{meas} = 70 dBµV
- V₀ = V'_{meas} + 16 dB (transformer ratio N1:N2 and transformer loss
- $G_v = 20 \log(V_0 / V_i) + 1 dB (1 dB = insertion loss of balun)$

5.5.3 Matching circuit for optimum noise figure in LOW band



For $f_{RF} = 50 \text{ MHz}$

■ loss = 0 dB

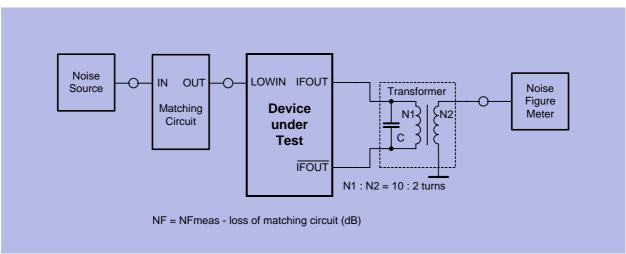
■ image suppression = 16 dB

For $f_{RF} = 150 \text{ MHz}$

■ loss = 1.3 dB

■ image suppression = 13 dB

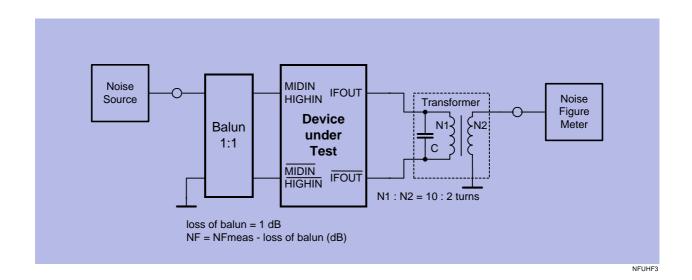
5.5.4 Noise figure (NF) measurement in LOW band



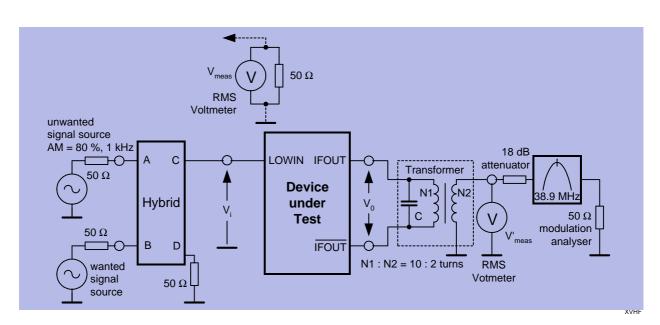
NFVHF



5.5.5 Noise figure (NF) measurement in MID and HIGH bands

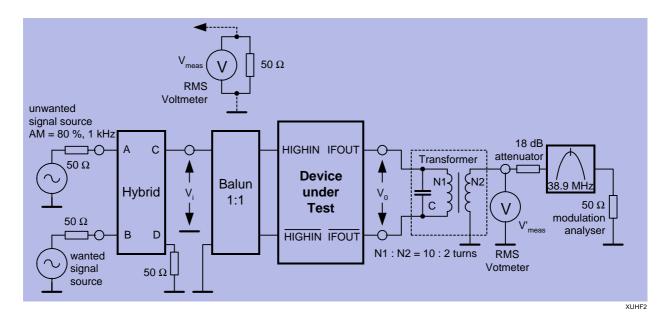


5.5.6 Cross modulation measurement in LOW band



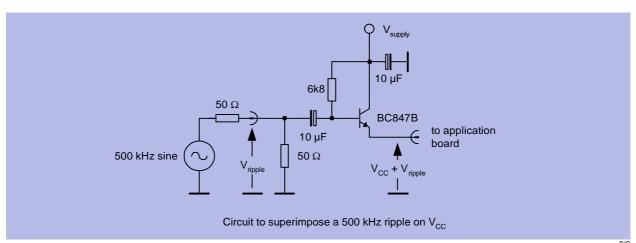
- $Z_i >> 50 \Omega => V_i = 2 \times V_{meas}$
- V'_{meas} = V₀ 16 dB (transformer ratio N1:N2 and transformer loss)
- wanted output signal at f_{pix}, V_o = 100 dBµV
- unwanted output signal at f_{snd}

5.5.7 Cross modulation measurement in MID and HIGH bands



- V'_{meas} = V₀ 16 dB (transformer ratio N1:N2 and transformer loss)
- wanted output signal at f_{pix}, V_o = 100 dBμV
- unwanted output signal at f_{snd}

5.5.8 Ripple susceptibility measurement



KIF